

Silicon NPN Power Transistors

2SC1913 2SC1913A

DESCRIPTION

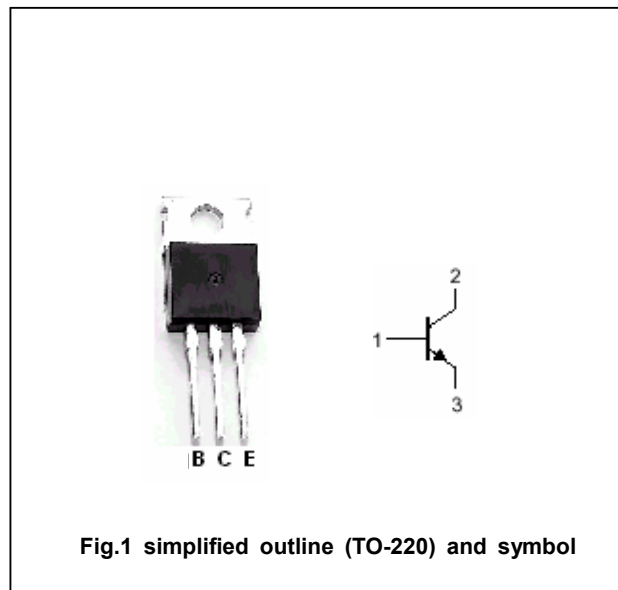
- With TO-220 package
- Complement to type 2SA913/913A
- Large collector power dissipation
- High V_{CE0}

APPLICATIONS

- Audio frequency high power driver

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC1913	150	V
		2SC1913A	180	
V_{CEO}	Collector-emitter voltage	2SC1913	150	V
		2SC1913A	180	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1	A
I_{CM}	Collector current-peak		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	15	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC1913	I _C =0.1mA, I _B =0	150			V
		2SC1913A		180			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =10μA, I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	2SC1913	I _C =0.3A; I _B =30mA			1.0	V
		2SC1913A				1.5	
V _{BEsat}	Base-emitter saturation voltage		I _C =0.3A; I _B =30mA			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =120V; I _E =0			1	μA
I _{EBO}	Emitter cut-off current		V _{EB} =4V; I _C =0			1	μA
h _{FE-1}	DC current gain		I _C =150mA; V _{CE} =10V	65		330	
h _{FE-2}	DC current gain		I _C =500mA; V _{CE} =5V	50			
C _{OB}	Output capacitance		I _E =0; V _{CB} =100V; f=1MHz			15	pF
f _T	Transition frequency		I _C =50mA; V _{CE} =10V		120		MHz

◆ h_{FE-1} Classifications

P	Q	R	S
65-110	90-155	130-220	185-330

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PACKAGE OUTLINE

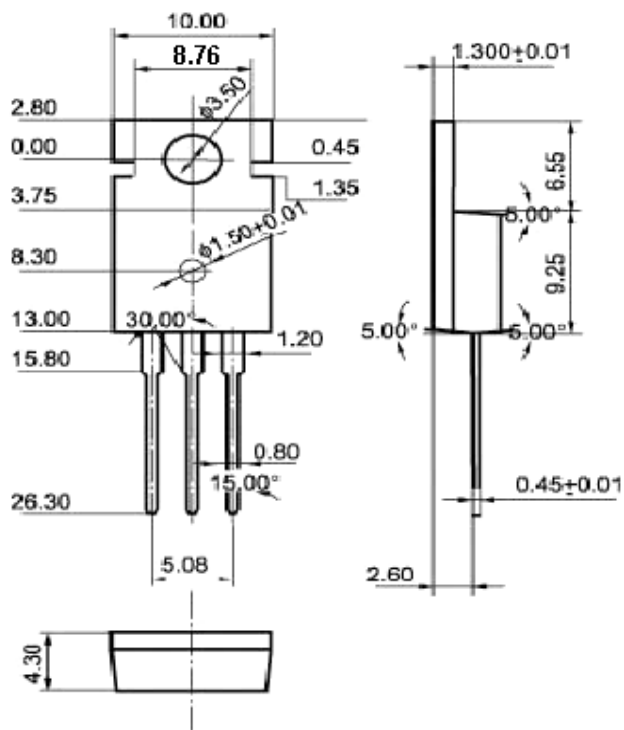


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)